

- AMR Switching-Sensor
- TDFN Outline 2.5x2.5x0.8 mm<sup>3</sup>
- Temperature Compensated Switching Point
- Low Power Consumption

#### **DESCRIPTION**

The MS32 is a magnetic field sensor which is built in the form of a Wheatstone bridge. Each of its four resistors is made from *Permalloy*, a material that shows the *anisotropic magnetoresistance effect*. An unidirectional magnetic field in the surface parallel to the chip (x-y plane) along the y-axis will deliver a field dependent output signal. A **magnetic switching point**, which is almost **independent on temperature** is typically set to Hs=1.85 kA/m. In addition, the characteristic curve is linear over a wide magnetic field range. Thus, the new MS32 simplifies the adaption of the sensor to different mechanical and magnetical environments. The sensor die is packaged in a modern TDFN package.

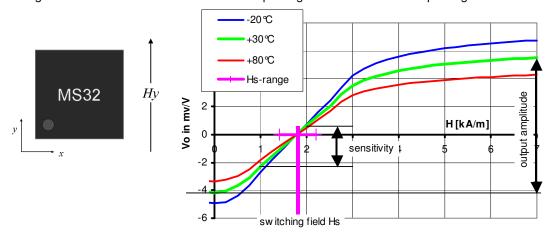


Figure 1: Characteristic curves for MS32 at different ambient temperatures (-20 ℃, +30 ℃, +80 ℃)

#### **FEATURES**

- Sensor Based on Solid State Magnetoresistance Effect
- Unipolar Signal Output
- Linear Field Response
- High Sensitivity, Low Hysteresis
- Temperature Compensated Switching Point
- Low Power Consumption Due to High Bridge Resistance
- Supply Voltage up to 30 V Allowed
- Small TDFN Package

#### **APPLICATIONS**

Contactless Position (Presence, Open/Close) Detection In :

- Industrial
- Consumer
- Automotive

Applications, like:

- Small Stroke Pneumatic Cylinders
- Cover Positions of Notebooks and Mobiles
- Doors, etc.

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### **CHARACTERISTIC VALUES**

Parameter	Condition	Symbol	Min	Тур	Max	Unit
Mechanical dimensions		•			,	
Length		Х		2.5		mm
Width		Υ		2.5		mm
Height		Z		0.75		mm
Pad size				0.25 x 0.30		mm <sup>2</sup>
Operating limits		•			,	
Max. supply voltage		V <sub>CC, MAX</sub>			30	V
Operating temperature		T <sub>OP</sub>	-25		+85	℃
Storage temperature		T <sub>ST</sub>	-25		+125	∞

Parameter	Condition	Symbol	Min	Тур	Max	Unit
Sensor specification ( $V_{CC} = 5 \text{ V}, T = 30 ^{\circ}\text{C}$ )						
Supply voltage		V <sub>CC</sub>		5	30	kA/m
Resistance		R <sub>B</sub>	10300	11500		Ω
Offset		V <sub>OFF</sub> /V <sub>CC</sub>		-4	-1.5	mV/V
Sensitivity	1)	S	2	3		(mV/V)/(kA/m)
Output amplitude	2)	V <sub>MAX</sub>	8			deg
Hysteresis (@ V <sub>0</sub> =0) 3)	)	Hyst.			0.9	deg
Sensor specification (T = -25 °C; +85 °C; Conditions A & B) 6)						
TC of amplitude		TCSV	-0.36	-0.32	-0.28	%/K
TC of bridge resistance	9	TCBR	+0.27	+0.32	+0.37	%/K
Switching field 5)	4)	Hs	1.40	1.85	2.30	kA/m

All parameters are measured on wafer level.

- 1) average gradient in the range 1.0 2.0 kA/m
- 2) difference between output voltage/supply voltage measured at H = 7 kA/m and H = 0 kA/m
- 3) hysteresis [in kA/m] = hysteresis [in mV/V] /S
- 4) switching voltage = 0 mV/V
- 5) switching field = magnetic field at switching voltage
- 6) values at −25 °C can be determined by linear extrapolation from +30 °C- and +85 °C-values.

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# **MEASUREMENT CONDITIONS**

Parameter	Symbol	Unit	Condition	
A. Set Up Conditions				
ambient temperature	Т	℃	T = 23 +/- 5 °C (unless otherwise noted)	
supply voltage	V <sub>CC</sub>	V	V <sub>CC</sub> = 5 V	
applied magnetic field	H <sub>Y</sub>	kA/m	$H_Y = -7 + 7 \text{ kA/m}$ ; along y-direction; $ H_X  < 100 \text{ A/m}$ Pre-magnetization along x-direction with $H_X >= 3 \text{ kA/m}$	
B. Parameter Definitions (T= -25 °C, +85 °C) see characteristic values 6)				
ambient temperatures	Т	℃	$T_1 = -25$ , $T_0 = +30$ , $T_2 = +85$ °C	
TC of amplitude	TCSV	%/K	$TCV = \frac{1}{(T_2 - T_1)} \cdot \frac{V_a(T_2) - V_a(T_1)}{V_a(T_1)} \cdot 100\%$	
TC of resistance	TCBR	%/K	$TCR = \frac{1}{(T_2 - T_1)} \cdot \frac{R(T_2) - R(T_1)}{R(T_1)} \cdot 100\%$	
TC of offset	TCV <sub>OFF</sub>	μV/(VK)	$TCVoff = \frac{Voff(T_2) - Voff(T_1)}{(T_2 - T_1)}$	

## **BLOCK DIAGRAM**

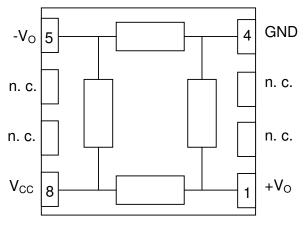


Figure 1: internal and external connections (TDFN, Chip)

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# **SENSOR OUTLINE**

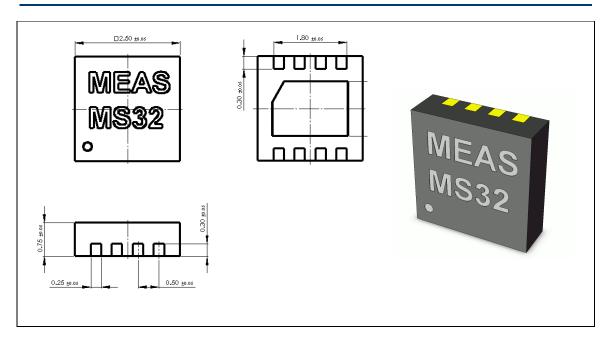


Figure 2: TDFN-outline

#### Pin assignment:

Pin	Symbol	Function	
1	+V <sub>O</sub>	positive output bridge	
2	n. c.	not connected	
3	n. c.	not connected	
4	GND	ground	
5	-V <sub>O</sub>	negative output bridge	
6	n. c.	not connected	
7	n. c.	not connected	
8	V <sub>CC</sub>	supply voltage bridge	

The bottom plate is designated to be a heat sink. It has no electrical connection to any pin. The sensitive area is positioned in the center of the package.

#### TAPE AND REEL PACKAGING INFORMATION

Description	Size/Quantity	Note
Reel	7"	
Units/reel	3,000	MOQ
Pin 1 orientation on tape	Top-right of sprocket hole side	

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### **ORDERING INFORMATION**

DEVICE	PACKAGE	PART NUMBER
Chip MS32 1)	wafer undiced	G-MRCH-022
MS32G 2)	TDFN 2.5 x 2.5	G-MRCH-017

- 1) MOQ is 1 wafer
- 2) MOQ is 1 reel

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